



#### P-CHANNEL ENHANCEMENT MODE MOSFET

#### **Product Summary**

V <sub>(BR)DSS</sub>	R <sub>DS(on)</sub>	<b>Ι</b> <sub>D</sub> Τ <sub>A</sub> = +25°C
	700mΩ @ $V_{GS}$ = -4.5V	-460mA
-20V	900mΩ @ V <sub>GS</sub> = -2.5V	-420mA
	1300mΩ @ V <sub>GS</sub> = -1.8V	-350mA

#### **Description and Applications**

This new generation MOSFET is designed to minimize the on-state resistance ( $R_{DS(on)}$ ) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- DC-DC Converters
- Load Switch
- Power Management Functions

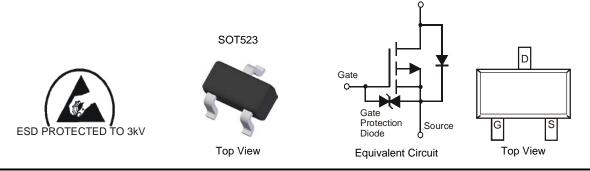
#### **Features and Benefits**

- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 standards for High Reliability

#### **Mechanical Data**

- Case: SOT523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe. Solderable per MIL-STD-202, Method 208<sup>(3)</sup>
- Terminal Connections: See Diagram
- Weight: 0.002 grams (approximate)

Drain



## Ordering Information (Note 3)

Case	Packaging
SOT523	3000/Tape & Reel
	SOT523

No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
See http://www.diodes.com/quality/lead\_free.htmlfor more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free.

Alalogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and</li>
<1000ppm antimony compounds.</li>

For packaging details, go to our website at http://www.diodes.com/products/packages.html.

#### **Marking Information**

PA1	ΥM

PA1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: W = 2009)

M = Month (ex: 9 = September)

Date	Code	Key

Notes:

Date Code Key												
Year	2009	20	10	2011	2012	20	13	2014	2015	20	16	2017
Code	W	)	X	Y	Z		4	В	С	]	)	E
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## Maximum Ratings @T<sub>A</sub> = +25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage		V <sub>DSS</sub>	-20	V	
Gate-Source Voltage		V <sub>GSS</sub>	±6	V	
Drain Current (Note 5)	Steady State	T <sub>A</sub> = +25°C T <sub>A</sub> = +85°C	ID	-0.46 -0.33	А
Pulsed Drain Current (Note 6)		I <sub>DM</sub>	-6	А	

#### Thermal Characteristics @TA = +25°C unless otherwise specified

Characteristic	Symbol	Value	Units
Total Power Dissipation (Note 5)	PD	0.27	W
Thermal Resistance, Junction to Ambient (Note 5)	R <sub>0JA</sub>	461	°C/W
Operating and Storage Temperature Range	T <sub>J,</sub> T <sub>STG</sub>	-55 to +150	C°

#### Electrical Characteristics @TA = +25°C unless otherwise specified

Characteristic	Cumpheal	Min	<b>T</b>	Max	11	Toot Condition
	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)			<b></b>			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	-	-	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	IDSS	-	-	-100	nA	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	-	-	±2.0	μA	$V_{GS} = \pm 4.5 V$ , $V_{DS} = 0 V$
ON CHARACTERISTICS (Note 7)						-
Gate Threshold Voltage	V <sub>GS(th)</sub>	-0.5	-	-1.0	V	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$
			0.5	0.7		V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -350mA
Static Drain-Source On-Resistance	R <sub>DS</sub> (ON)	-	0.7	0.9	Ω	V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -300mA
			1.0	1.3		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -150mA
Forward Transfer Admittance	Y <sub>fs</sub>	-	0.9	-	S	V <sub>DS</sub> = -10V, I <sub>D</sub> = -250mA
Diode Forward Voltage	V <sub>SD</sub>		-0.8	-1.2	V	$V_{GS} = 0V, I_{S} = -150mA$
DYNAMIC CHARACTERISTICS (Note 8)						
Input Capacitance	Ciss	-	59.76	-	pF	
Output Capacitance	Coss	-	12.07	-	pF	V <sub>DS</sub> = -16V, V <sub>GS</sub> = 0V, f = 1.0MHz
Reverse Transfer Capacitance	Crss	-	6.36	-	pF	
Total Gate Charge	Qq	-	580	-	рС	
Gate-Source Charge	Q <sub>as</sub>	-	104	-	рС	$V_{GS} = -4.5V, V_{DS} = -10V,$
Gate-Drain Charge	Q <sub>qd</sub>	-	125	-	рС	$-I_{\rm D} = -250 {\rm mA}$
Turn-On Delay Time	t <sub>D(on)</sub>	-	5.1	-	ns	
Turn-On Rise Time	tr	-	8.1	-	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(off)</sub>	-	28.4	-	ns	$R_{L} = 47\Omega, R_{G} = 10\Omega,$ $D_{D} = -200 \text{mA}$
Turn-Off Fall Time	t <sub>f</sub>	-	20.7	-	ns	

Notes: 5. For a device surface mounted on a minimum recommended pad layout of an FR4 PCB, in still air conditions; the device is measured when operating in steady-state condition.

6. Same as note 5, except the device is pulsed at duty cycle of 1% for a pulse width of 10 $\mu s.$ 

7. Measured under pulsed conditions to minimize self-heating effect. Pulse width  $\leq$  300µs; duty cycle  $\leq$  2%.

8. For design aid only, not subject to production testing.





2

2.5

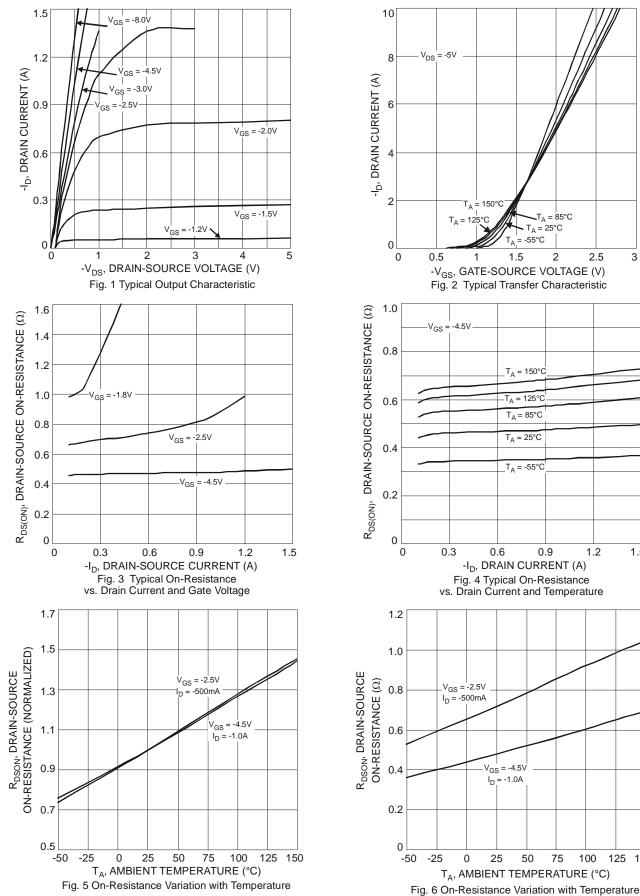
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75

100

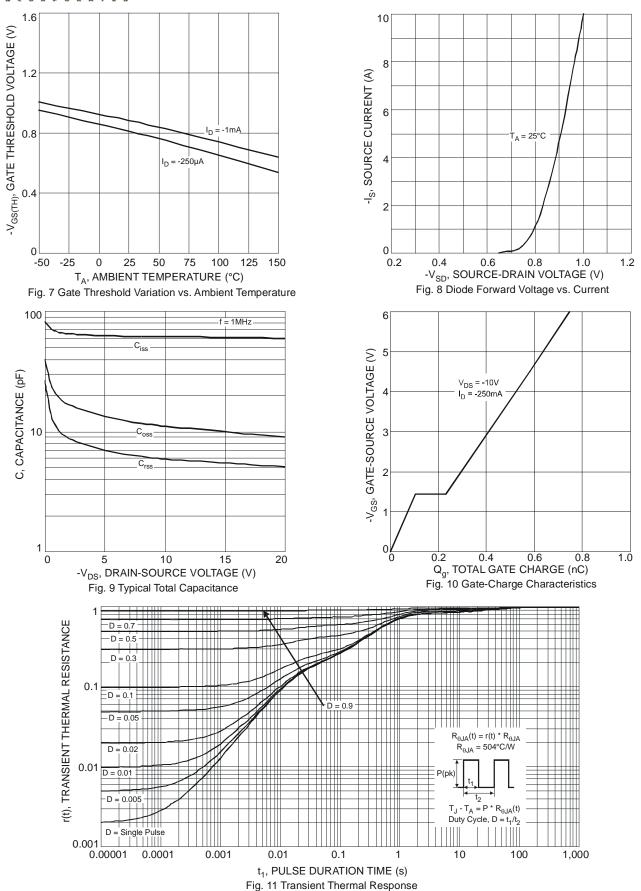
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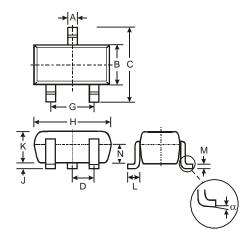






## **Package Outline Dimensions**

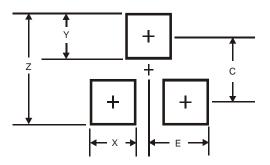
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT523						
Dim	Min	Max	Тур			
Α	0.15	0.30	0.22			
В	0.75	0.85	0.80			
С	1.45	1.75	1.60			
D		_	0.50			
G	0.90	1.10	1.00			
Н	1.50	1.70	1.60			
J	0.00	0.10	0.05			
κ	0.60	0.80	0.75			
L	0.10	0.30	0.22			
М	0.10	0.20	0.12			
Ν	0.45	0.65	0.50			
α	0°	8°				
All	All Dimensions in mm					

#### **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for latest version.



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Y	0.51
С	1.3
E	0.7



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